## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention

METHOD OF FABRICATING A CMOS DEVICE WITH DUAL METAL GATE ELECTRODES

Application Number:

10/826665

Confirmation Number:

9608

First Named Applicant:

CHANG PARK

Attorney Docket Number:

61472-0308425

Art Unit:

Examiner:

Search string:

(6653698 or 6352913).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	. Patentee	Kind	Class	Subclass
MIST	1	6653698	2003-11-25	LEE ET AL.	B2	257	407
mDI	2	6352913	2002-03-05	MISTRY ET AL.	B1	438	587

## Signature

Examiner Name	Date
Moneyo Harrish	3/17/06